

**Notice of References Cited**

Application/Control No.

09/600,546

Applicant(s)/Patent Under

Reexamination

CHAPPERT ET AL.

Examiner

Martin J Angebranndt

Art Unit

1756

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.